

# Daoqian Zhu

## List of Publications by Year in descending order

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27  
papers

1,274  
citations

471061

17  
h-index

610482

24  
g-index

27  
all docs

27  
docs citations

27  
times ranked

1106  
citing authors

#	ARTICLE	IF	CITATIONS
1	Antiferromagnetic spintronics: An overview and outlook. <i>Fundamental Research</i> , 2022, 2, 522-534.	1.6	39
2	Observation of magnetic droplets in magnetic tunnel junctions. <i>Science China: Physics, Mechanics and Astronomy</i> , 2022, 65, .	2.0	11
3	Unconventional applications of skyrmions. , 2021, , 393-416.		0
4	Spinâ€Torque Memristors Based on Perpendicular Magnetic Tunnel Junctions for Neuromorphic Computing. <i>Advanced Science</i> , 2021, 8, 2004645.	5.6	34
5	Experimental Demonstration of NAND-Like Spin-Torque Memory Unit. <i>IEEE Electron Device Letters</i> , 2021, 42, 513-516.	2.2	18
6	Sub-ns Field-Free Switching in Perpendicular Magnetic Tunnel Junctions by the Interplay of Spin Transfer and Orbit Torques. <i>IEEE Electron Device Letters</i> , 2021, 42, 704-707.	2.2	33
7	Spintronics for Energy- Efficient Computing: An Overview and Outlook. <i>Proceedings of the IEEE</i> , 2021, 109, 1398-1417.	16.4	112
8	Computational Study for Spin-orbit Torque Magnetic Random Access Memory. , 2021, , .		3
9	A Comparative Cross-layer Study on Racetrack Memories. <i>ACM Journal on Emerging Technologies in Computing Systems</i> , 2020, 16, 1-17.	1.8	14
10	Giant Perpendicular Magnetic Anisotropy in Moâ€Based Doubleâ€Interface Free Layer Structure for Advanced Magnetic Tunnel Junctions. <i>Advanced Electronic Materials</i> , 2020, 6, 2000271.	2.6	26
11	Spinâ€orbit torque driven multi-level switching in He+ irradiated Wâ€CoFeBâ€MgO Hall bars with perpendicular anisotropy. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	19
12	Exchange bias switching in an antiferromagnet/ferromagnet bilayer driven by spinâ€orbit torque. <i>Nature Electronics</i> , 2020, 3, 757-764.	13.1	99
13	Stochastic Computing Implemented by Skyrmionic Logic Devices. <i>Physical Review Applied</i> , 2020, 13, .	1.5	39
14	Modulation of field-like spin orbit torque in heavy metal/ferromagnet heterostructures. <i>Nanoscale</i> , 2020, 12, 15246-15251.	2.8	27
15	Optoelectronic domain-wall motion for logic computing. <i>Applied Physics Letters</i> , 2020, 116, 252403.	1.5	5
16	Magnetic Skyrmion Spectrum Under Voltage Excitation and its Linear Modulation. <i>Physical Review Applied</i> , 2019, 12, .	1.5	4
17	Field-free spinâ€orbit-torque switching of perpendicular magnetization aided by uniaxial shape anisotropy. <i>Nanotechnology</i> , 2019, 30, 375202.	1.3	30
18	Modulation of Heavy Metal/Ferromagnetic Metal Interface for Highâ€Performance Spintronic Devices. <i>Advanced Electronic Materials</i> , 2019, 5, 1900134.	2.6	64

#	ARTICLE	IF	CITATIONS
19	Proposal of Toggle Spin Torques Magnetic RAM for Ultrafast Computing. IEEE Electron Device Letters, 2019, 40, 726-729.	2.2	74
20	A compact skyrmionic leakyâ€“integrateâ€“fire spiking neuron device. Nanoscale, 2018, 10, 6139-6146.	2.8	96
21	High-Density NAND-Like Spin Transfer Torque Memory With Spin Orbit Torque Erase Operation. IEEE Electron Device Letters, 2018, 39, 343-346.	2.2	119
22	Size dependence of the spin-orbit torque induced magnetic reversal in W/CoFeB/MgO nanostructures. Applied Physics Letters, 2018, 112, 142410.	1.5	17
23	Skyrmion Racetrack Memory With Random Information Update/Deletion/Insertion. IEEE Transactions on Electron Devices, 2018, 65, 87-95.	1.6	41
24	Field-free switching of a perpendicular magnetic tunnel junction through the interplay of spinâ€“orbit and spin-transfer torques. Nature Electronics, 2018, 1, 582-588.	13.1	304
25	A Comparative Study on Racetrack Memories: Domain Wall vs. Skyrmion. , 2018, , .		10
26	Complementary Skyrmion Racetrack Memory Enables Voltage-Controlled Local Data Update Functionality. IEEE Transactions on Electron Devices, 2018, 65, 4667-4673.	1.6	7
27	Skyrmion dynamics in width-varying nanotracks and implications for skyrmionic applications. Applied Physics Letters, 2017, 111, .	1.5	29